L Number	Hits	Search Text	DB	Time stamp
13	5041		USPAT;	2004/04/18 20:23
		(438/584) or (438/706) or (438/758) or	US-PGPUB;	
		(438/795) or (438/909) or (438/935)).CCLS.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/04/18 20:2:
14	37845	(hold or holding) near portion	USPAT; US-PGPUB;	2004/04/18 20.2.
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
15	20782	 SOI or (silicon adj on adj insulator)	USPAT;	2004/04/18 20:23
12	20702	Sol of (silicon da) on day imparatory	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
16	23846	reducing near atmosphere	USPAT;	2004/04/18 20:2
		-	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	4. 4
17	805976	hydrogen	USPAT;	2004/04/18 20:2
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_	(4) 33 (60)	IBM_TDB	2004/04/18 20:2
18	2	` · ·	USPAT; US-PGPUB;	2004/04/18 20:2
1		or (silicon adj on adj insulator))	EPO; JPO;	
			DERWENT;	
-			IBM TDB	
19	96	((hold or holding) near portion) and (SOI or	USPAT;	2004/04/18 20:2
19	70	(silicon adj on adj insulator))	US-PGPUB;	
		(81118811 445) 4111414141,	EPO; JPO;	
		,	DERWENT;	
			IBM_TDB	
20	1	(((hold or holding) near portion) and (SOI	USPAT;	2004/04/18 20:2
		or (silicon adj on adj insulator))) and	US-PGPUB;	
		(reducing near atmosphere)	EPO; JPO;	
			DERWENT;	
	_	////\\\\\\\\\.	IBM_TDB	2004/04/18 20:2
21	1	((((hold or holding) near portion) and (SOI	USPAT; US-PGPUB;	2004/04/18 20:2
		or (silicon adj on adj insulator))) and (reducing near atmosphere)) and hydrogen	EPO; JPO;	
		(reducing hear acmosphere)) and hydrogen	DERWENT;	
			IBM TDB	
_	34	silicon adj boat	USPAT;	2002/11/20 18:4
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	34	silicon adj boat	USPAT;	2002/11/20 11:0
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/11/00 10 1
-	60174	silicon adj carbide	USPAT;	2002/11/20 18:1
			US-PGPUB; EPO; JPO;	
		,	DERWENT;	
			IBM TDB	
_	92082	cvd	USPAT;	2002/11/20 18:1
-	92002	CVG	US-PGPUB;	2502,11,20 10.1
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2120	(silicon adj carbide) same cvd	USPAT;	2002/11/20 18:1
	-120		US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	

-	66246	boat	USPAT; US-PGPUB;	2002/11/20 18:18
			I DDA IDA.	1
1 1			EPO; JPO; DERWENT;	
i i	ŀ		IBM TDB	·
	4.7	((silicon adj carbide) same cvd) same boat	USPAT;	2002/11/20 18:18
-	41	((SIIICOII au) Carbide) same evu, same sour	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
-			IBM_TDB	
_	34	silicon adj boat	USPAT;	2002/11/21 19:44
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(11 11 11 11 11 11 11 11 11 11 11 11 11	IBM_TDB USPAT;	2002/11/20 18:43
-	1	<pre>(((silicon adj carbide) same cvd) same boat) and (silicon adj boat)</pre>	US-PGPUB;	2002/11/20 10:13
		and (Silicon adj boat)	EPO; JPO;	
			DERWENT;	
		•	IBM TDB	
_	74	(((silicon adj carbide) same cvd) same boat)	USPAT;	2002/11/20 18:43
	'*	or (silicon adj boat)	US-PGPUB;	
		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/11/21 10:42
-	14400	soi	USPAT;	2002/11/21 19:43
			US-PGPUB; EPO; JPO;	
	[•	DERWENT;	
			IBM TDB	
	34	silicon adj boat	USPAT;	2002/11/21 19:44
-	34	SITTOON and Done	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	soi same (silicon adj boat)	USPAT;	2002/11/21 19:46
			US-PGPUB;	
		•	EPO; JPO;	
			DERWENT; IBM TDB	
1	1116000		USPAT;	2002/11/21 19:50
_	1146922	semiconductor	US-PGPUB;	2002, 11, 21 15:00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	(silicon adj boat) same semiconductor	USPAT;	2002/11/21 19:46
		_	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		aadd on odd inculates	IBM_TDB USPAT;	2003/11/07 18:28
-	12	semiconductor adj on adj insulat\$3	US-PGPUB;	2003/11/0/ 10:20
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	14562	soi	USPAT;	2002/12/02 11:04
	-1002		US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	2002/12/02 11 01
-	508529	transistor	USPAT;	2002/12/02 11:04
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
	3801	soi same transistor	USPAT;	2002/12/02 11:04
_	3001	SOT Same Clansiscot	US-PGPUB;	
			EPO; JPO;	
•		F		4
			DERWENT;	

-	60532	silicon adj carbide	USPAT;	2002/12/02 11:04
		-	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
	10	(soi same transistor) same (silicon adj	USPĀT;	2003/11/07 18:28
		carbide)	US-PGPUB;	
!			EPO; JPO;	
			DERWENT; IBM TDB	
	15468	soi or (silicon near2 insulator)	USPAT;	2003/05/18 20:25
-	13400	BOI OI (BILICOM MEGIZ IMPAZADOZ)	US-PGPUB	
_	265	silicon near2 boat	USPAT;	2003/05/18 20:25
			US-PGPUB	2003/05/18 20:26
-	14	(soi or (silicon near2 insulator)) and	USPAT; US-PGPUB	2003/05/16 20:26
	13	<pre>(silicon near2 boat) ((soi or (silicon near2 insulator)) and</pre>	USPAT;	2003/05/18 20:27
_	13	(silicon near2 boat)) and @ad<20020307	US-PGPUB	, ,
_	1	("6468884").PN.	USPAT;	2003/10/29 10:53
		(100/100)	US-PGPUB	2004/04/18 20:21
_	4619	((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or	USPAT; US-PGPUB;	2004/04/10 20:21
		(438/584) or (438/706) or (438/756) or (438/795) or (438/909) or (438/935)).CCLS.	EPO; JPO;	
		(130/193/ Of (130/909) Of (130/933//.ccab.	DERWENT;	
			IBM_TDB	
-	405	(silicon or ((single near2 crystal) adj	USPAT;	2003/11/07 14:33
		silicon) or (poly near2 silicon) or (silicon	US-PGPUB; EPO; JPO;	
		near2 carbide)) near2 boat	DERWENT;	
	1		IBM TDB	
-	20		USPAT;	2003/11/07 14:26
		(438/584) or (438/706) or (438/758) or	US-PGPUB;	
		(438/795) or (438/909) or (438/935)).CCLS.)	EPO; JPO; DERWENT;	
		and ((silicon or ((single near2 crystal) adj silicon) or (poly near2 silicon) or (silicon	IBM TDB	
		near2 carbide)) near2 boat)		
_	100	(silicon near2 carbide) near2 boat	USPAT;	2003/11/07 18:29
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	8	(((438/149) or (438/311) or (438/459) or	USPAT;	2003/11/07 14:33
		(438/584) or (438/706) or (438/758) or	US-PGPUB;	
		(438/795) or (438/909) or (438/935)).CCLS.)	EPO; JPO;	
		and ((silicon near2 carbide) near2 boat)	DERWENT; IBM TDB	
_	0	6296709.URPN.	USPAT	2003/11/07 14:37
_	5	("4640223" "4964378" "5001327"	USPAT	2003/11/07 14:37
		"5029554" "6139642").PN.	Habar	2002/11/07 10 20
	7513	(soi or(semiconductor adj on adj insulat\$3))	USPAT;	2003/11/07 18:29
-	/513			
-	/513	near2 substrate	US-PGPUB; EPO: JPO:	
-	/513		EPO; JPO; DERWENT;	
-	7513	near2 substrate	EPO; JPO; DERWENT; IBM_TDB	
-	100		EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/11/07 18:30
-		near2 substrate	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/11/07 18:30
-		near2 substrate	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/07 18:30
-		near2 substrate	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/11/07 18:30
-		near2 substrate (silicon near2 carbide) near2 boat ((soi or(semiconductor adj on adj	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/11/07 18:30
-	100	near2 substrate (silicon near2 carbide) near2 boat ((soi or(semiconductor adj on adj insulat\$3)) near2 substrate) same ((silicon	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	
-	100	near2 substrate (silicon near2 carbide) near2 boat ((soi or(semiconductor adj on adj	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	